

N-channel TrenchMOS SiliconMAX standard level FET 3 October 2013 Product data sheet

1. General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

2. Features and benefits

- Higher operating power due to low thermal resistance
- Suitable for high frequency applications due to fast switching characteristics

3. Applications

- Class D amplifier
- DC-to-DC converters
- Motion control
- Switched-mode power supplies

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C		-	-	150	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u> ; <u>Fig. 3</u>		-	-	43	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	113	W
Static charact	eristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 12 A; T _j = 25 °C; <u>Fig. 9; Fig. 10</u>		-	46	59	mΩ
Dynamic characteristics							
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 12 A; V _{DS} = 75 V; <u>Fig. 11; Fig. 12</u>		-	9.1	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UTA
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PSMN059-150Y	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN059-150Y	059150

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	150	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}; R_{GS} = 20 \Omega$	-	150	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1; Fig. 3</u>	-	43	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	-	27.7	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3	-	129	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	113	W
T _{stg}	storage temperature		-55	150	°C

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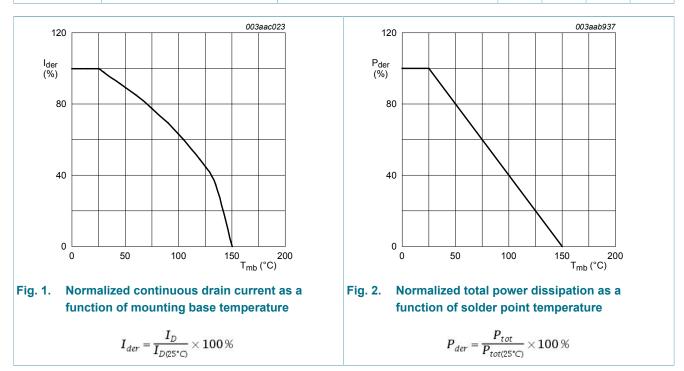
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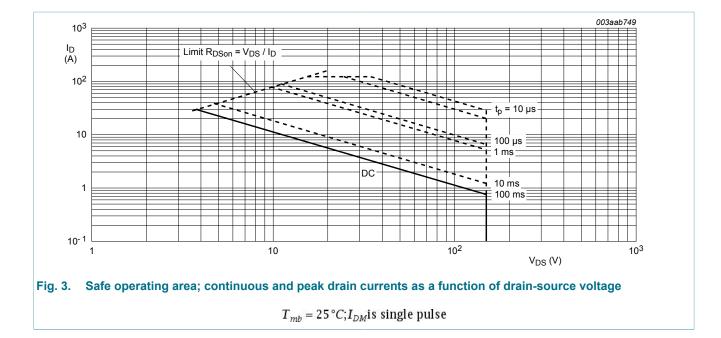
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Symbol	Parameter	Conditions	Min	Мах	Unit	
Tj	junction temperature		-55	150	°C	
Source-drain diode						
I _S	source current	T _{mb} = 25 °C	-	52	А	
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$	-	208	А	
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; I_{D} = 12.1 \; A; \\ V_{sup} \leq 150 \; V; \; unclamped; \; t_{p} = 0.21 \; ms; \\ R_{GS} = 50 \; \Omega \end{array}$	-	255	mJ	



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9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	mounted on a printed-circuit board; vertical in still air; Fig. 4	-	-	1.1	K/W

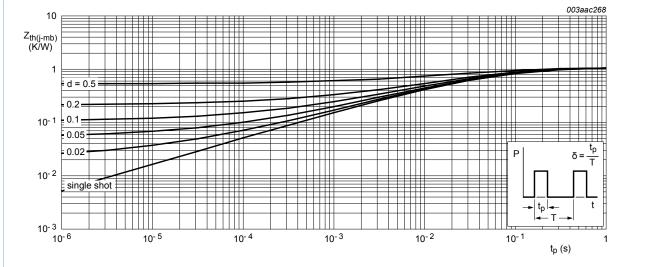


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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10. Characteristics

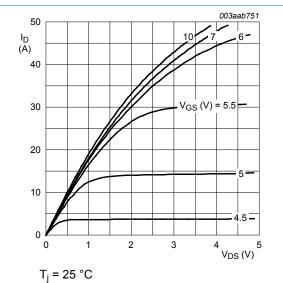
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		I			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	150	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	133	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 7; Fig. 8	2	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 150 °C; Fig. 7; Fig. 8	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 7; Fig. 8	-	-	4.4	V
I _{DSS}	drain leakage current	V_{DS} = 120 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
		V _{DS} = 120 V; V _{GS} = 0 V; T _j = 150 °C	-	-	100	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon} drain-source on-state resistance		V _{GS} = 10 V; I _D = 12 A; T _j = 25 °C; Fig. 9; Fig. 10	-	46	59	mΩ
	V _{GS} = 10 V; I _D = 12 A; T _j = 150 °C; Fig. 9; Fig. 10	-	101	135	mΩ	
R _G	gate resistance	f = 1 MHz	-	1.1	-	Ω
Dynamic cł	naracteristics	I I				
Q _{G(tot)}	total gate charge	I_D = 12 A; V_{DS} = 75 V; V_{GS} = 10 V;	-	27.9	-	nC
Q _{GS}	gate-source charge	Fig. 11; Fig. 12	-	6.3	-	nC
Q _{GD}	gate-drain charge		-	9.1	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 12 A; V _{DS} = 75 V; <u>Fig. 11</u> ; <u>Fig. 12</u>	-	4.8	-	V
C _{iss}	input capacitance	V _{DS} = 30 V; V _{GS} = 0 V; f = 1 MHz;	-	1529	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 13</u>	-	208	-	pF
C _{rss}	reverse transfer capacitance		-	66	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 75 V; R _L = 3 Ω; V _{GS} = 10 V;	-	14.2	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega$	-	42	-	ns
t _{d(off)}	turn-off delay time		-	54.2	-	ns
t _f	fall time		-	11.1	-	ns
Source-dra	in diode	· · · · · · · · · · · · · · · · · · ·				
V _{SD}	source-drain voltage	I _S = 12 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 14</u>	-	0.9	1.2	V

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N-channel TrenchMOS SiliconMAX standard level FET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	reverse recovery time	$I_{\rm S}$ = 12 A; dI_{\rm S}/dt = -100 A/µs; V _{GS} = 0 V; V _{DS} = 30 V	-	67	-	ns
Q _r	recovered charge	$I_{\rm S}$ = 12 A; dI_{\rm S}/dt = -100 A/µs; V _{GS} = 0 V	-	226	-	nC





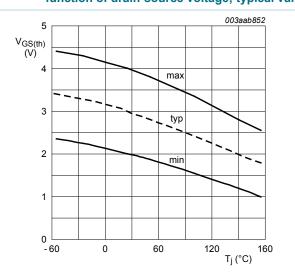
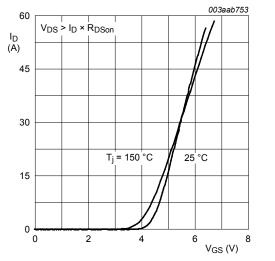


Fig. 7. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 m A; V_{DS} = V_{GS}$$



 $T_i = 25 \text{ °C}$ and 150 °C; $V_{DS} > I_D \times R_{DSon}$



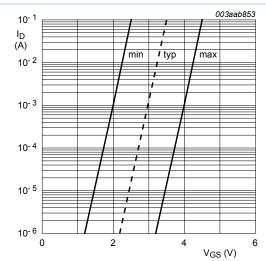


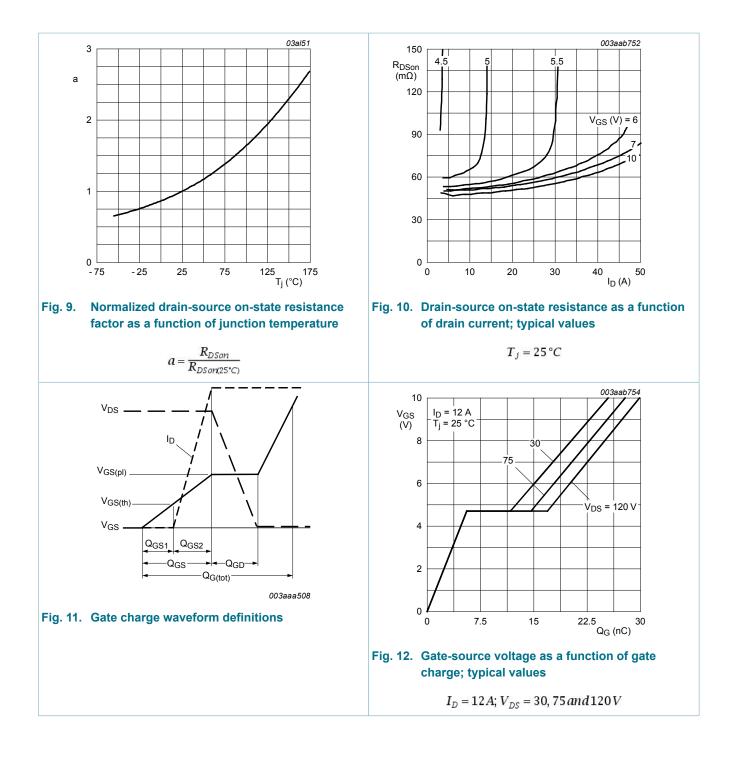
Fig. 8. Sub-threshold drain current as a function of gate-source voltage

 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

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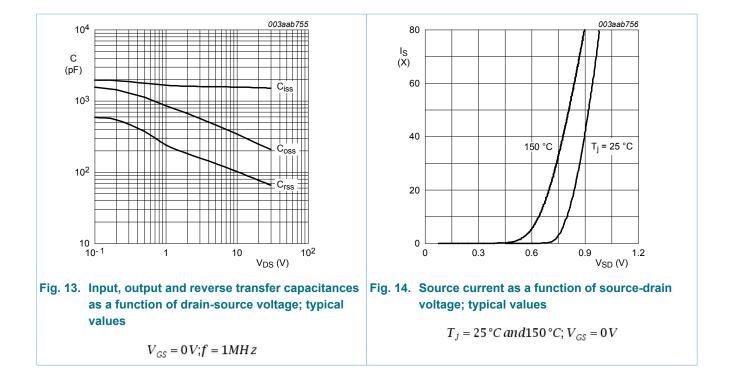
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7/12

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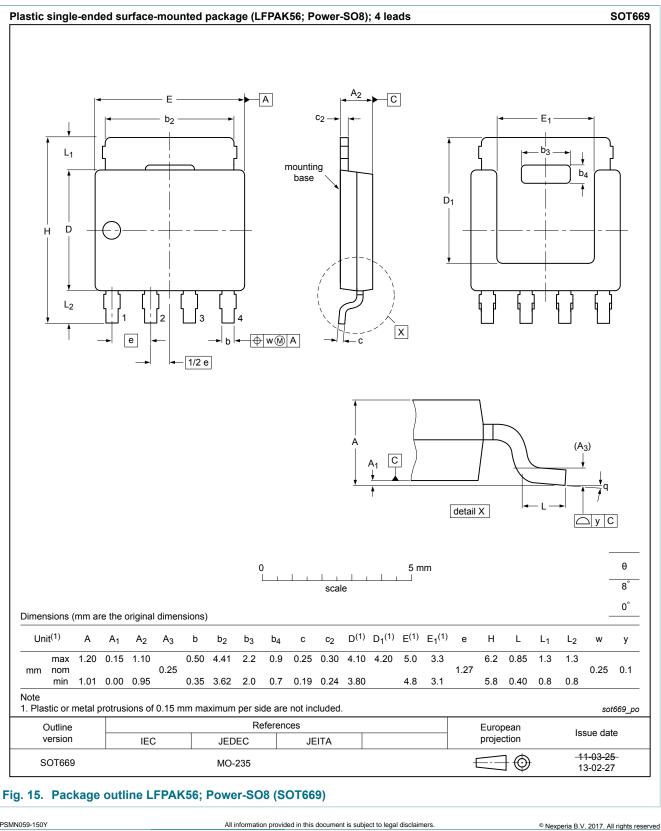
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N-channel TrenchMOS SiliconMAX standard level FET



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11. Package outline



PSMN059-150Y

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12. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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13. Contents

General description	1
Features and benefits	1
Applications	1
Quick reference data	1
Pinning information	2
Ordering information	2
Marking	2
Limiting values	2
Thermal characteristics	4
Characteristics	5
Package outline	9
Legal information	10
Data sheet status	10
Definitions	10
Disclaimers	10
Trademarks	11
	General description Features and benefits

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